

# STPS30SM60C

### Power Schottky rectifier

### Features

- High current capability
- Avalanche rated
- Low forward voltage drop
- High frequency operation

### Description

. . .

T<sub>i</sub> (max)

The STPS30SM60C is a dual diode Schottky rectifier, suited for high frequency switch mode power supply.

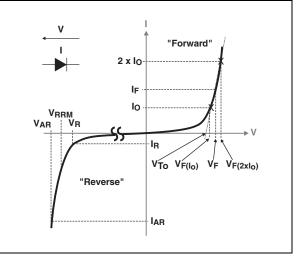
Packaged in TO-220AB, I<sup>2</sup>PAK and D<sup>2</sup>PAK, this device is intended to be used in notebook, game station and desktop adapters, providing in these applications a good efficiency at both low and high load.

	Table 1.   Device summary					
Symbol		Value				
ſ	I <sub>F(AV)</sub>	2 x 15 A				
	V <sub>RRM</sub>	60 V				
	V <sub>F</sub> (typ)	0.405 V				

150 °C

### A1.─ ► A2⊷ ► κ Δ2 **A1** D<sup>2</sup>PAK I<sup>2</sup>PAK STPS30SM60CG-TR STPS30SM60CR A2 ĸ A1 **TO-220AB** STPS30SM60CT





 V<sub>ARM</sub> and I<sub>ARM</sub> must respect the reverse safe operating area defined in *Figure 12*. V<sub>AR</sub> and I<sub>AR</sub> are pulse measurements (t<sub>p</sub> < 1 μs). V<sub>R</sub>, I<sub>R</sub>, V<sub>RRM</sub> and V<sub>F</sub>, are static characteristics

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#### **Characteristics** 1

Absolute ratings (limiting values, per diode, at  $T_{amb}$  = 25 °C unless Table 2. otherwise specified)

Symbol		Value	Unit			
V <sub>RRM</sub>	Repetitive peak reverse volt	tage			60	V
I <sub>F(RMS)</sub>	Forward rms current				40	А
	Average forward ourrent S.			Per diode	15	۸
I <sub>F(AV)</sub>	Average forward current, $\delta = 0.5$		T <sub>c</sub> = 130 °C	Per device	30	A
I <sub>FSM</sub>	Surge non repetitive forward current t <sub>p</sub> = 10 ms sine-wave			300	А	
P <sub>ARM</sub> <sup>(1)</sup>	Repetitive peak avalanche	power	T <sub>j</sub> = 25 °C, t <sub>p</sub>	= 1 µs	14400	W
V <sub>ARM</sub> <sup>(2)</sup>	Maximum repetitive peak avalanche voltage	t <sub>p</sub> < 1 μs, T <sub>j</sub> <	150 °C, I <sub>AR</sub> < 8	54 A	80	V
V <sub>ARM</sub> <sup>(2)</sup>	Maximum single-pulse peak avalanche voltage	t <sub>p</sub> < 1 μs, T <sub>j</sub> < 150 °C, I <sub>AR</sub> < 54 A			80	V
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C	
Тj	Maximum operating junction temperature <sup>(3)</sup>			150	°C	

For temperature or pulse time duration deratings, please refer to *Figure 4* and *5*. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

2. See Figure 12

 $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink 3.

#### Table 3. **Thermal parameters**

Symbol	Parameter	Value	Unit	
D	Junction to case	er diode	1.5	°C/W
R <sub>th(j-c)</sub>	total		0.85	0/ •••
R <sub>th(c)</sub>	Coupling	0.2	°C/W	

When the two diodes 1 and 2 are used simultaneously:

 $\Delta T_{i}$ (diode 1) = P(diode 1) x R<sub>th(i-c)</sub>(Per diode) + P(diode 2) x R<sub>th(c)</sub>



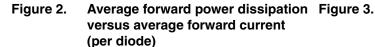
Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
ا <sub>B</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	$V_{R} = V_{RRM}$	-	15	65	μA
'R`´		T <sub>j</sub> = 125 °C		-	10	40	mA
	$V_{F}^{(2)} Forward voltage drop \begin{cases} T_{j} = 25 \text{ °C} \\ T_{j} = 125 \text{ °C} \\ T_{j} = 25 \text{ °C} \\ T_{j} = 25 \text{ °C} \\ T_{j} = 125 \text{ °C} \\ \end{array}  _{F} = 15 \text{ A}$	-	0.495	0.535			
V (2)		T <sub>j</sub> = 125 °C	if = 7.5 A	-	0.405	0.455	v
¥F` ´		T <sub>j</sub> = 25 °C	– I <sub>F</sub> = 15 A	-	0.565	0.625	v
		T <sub>j</sub> = 125 °C		-	0.505	0.570	

 Table 4.
 Static electrical characteristics (per diode)

1. Pulse test:  $t_p = 5 \text{ ms}, \delta < 2\%$ 

2. Pulse test:  $t_p = 380 \ \mu s, \ \delta < 2\%$ 

To evaluate the conduction losses use the following equation: P = 0.415 x  $I_{F(AV)}$  + 0.0103 x  ${I_F}^2_{(RMS)}$ 



Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)

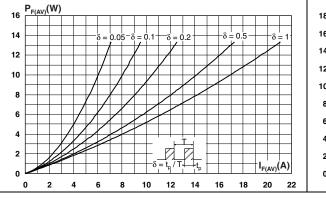


Figure 4. Normalized avalanche power derating versus pulse duration

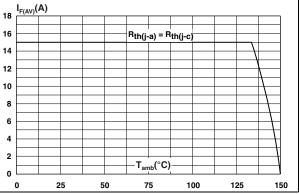
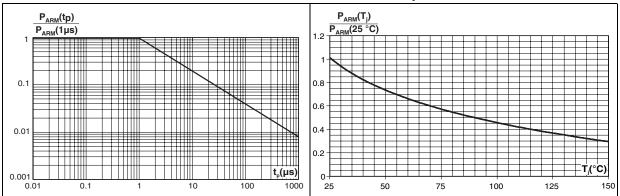
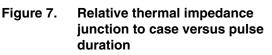


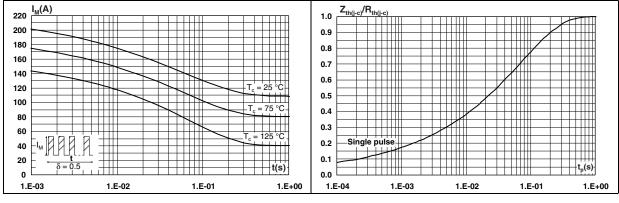
Figure 5. Normalized avalanche power derating versus junction temperature

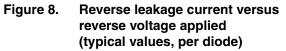


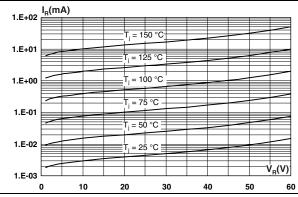


#### Figure 6. Non repetitive surge peak forward F current versus overload duration (maximum values, per diode)









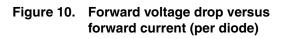


Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)

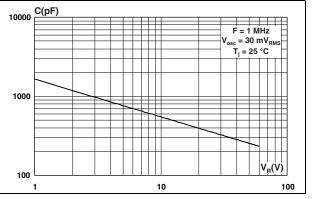
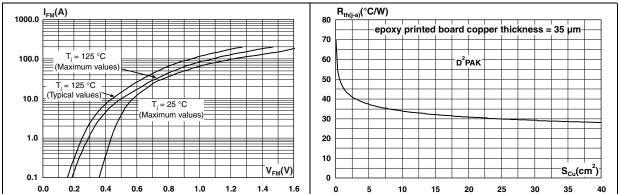


Figure 11. Thermal resistance junction to ambient versus copper surface under tab





J	<u></u>
60.0	I <sub>arm</sub> (A)
	I <sub>arm</sub> (V <sub>arm</sub> ) 150 °C, 1μs
55.0	
50.0	
45.0	
40.0	
40.0	
35.0	
30.0	Varm (V)
	80 85 90 95 100 105 110 115 120

Figure 12. Reverse safe operating area ( $t_p < 1 \ \mu s$  and  $T_i < 150 \ ^\circ C$ )



### 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK<sup>®</sup> is an ST trademark.

Table 5. TO-220AB dimensions

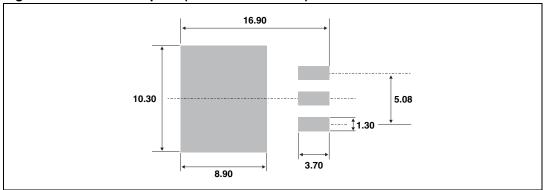
				Dimer	nsions	
		Ref.	Millin	neters	Inc	hes
			Min.	Max.	Min.	Max.
		А	4.40	4.60	0.173	0.181
		С	1.23	1.32	0.048	0.051
H2 Dia	A	D	2.40	2.72	0.094	0.107
		Е	0.49	0.70	0.019	0.027
	L7	F	0.61	0.88	0.024	0.034
L6		F1	1.14	1.70	0.044	0.066
		F2	1.14	1.70	0.044	0.066
F2		G	4.95	5.15	0.194	0.202
	D	G1	2.40	2.70	0.094	0.106
		H2	10	10.40	0.393	0.409
F→ ←		L2	16.4	Тур.	0.645	5 Тур.
G1,	M =	L4	13	14	0.511	0.551
	K→ → E	L5	2.65	2.95	0.104	0.116
G		L6	15.25	15.75	0.600	0.620
		L7	6.20	6.60	0.244	0.259
		L9	3.50	3.93	0.137	0.154
		М	2.6	Тур.	0.102	2 Тур.
		Dia.	3.75	3.85	0.147	0.151



			Dimer	nsions	
	Ref.	Millimeters		Inches	
		Min.	Max.	Min.	Max.
	А	4.40	4.60	0.173	0.181
	→ A1	2.49	2.69	0.098	0.106
$\begin{array}{c c} L2 \\ \hline \\ $	A2	0.03	0.23	0.001	0.009
	В	0.70	0.93	0.027	0.037
	B2	1.14	1.70	0.045	0.067
	C	0.45	0.60	0.017	0.024
	C2	1.23	1.36	0.048	0.054
$\begin{array}{c c} & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ \end{array}$	<u> </u>	8.95	9.35	0.352	0.368
G	E	10.00	10.40	0.393	0.409
A2	G	4.88	5.28	0.192	0.208
	L	15.00	15.85	0.590	0.624
Ţ*ŢW	L2	1.27	1.40	0.050	0.055
* FLAT ZONE NO LESS	L3	1.40	1.75	0.055	0.069
FLATZONE NO LESS	M	2.40	3.20	0.094	0.126
	R	0.40	) typ.	0.016	6 typ.
	V2	0°	8°	0°	8°

Table 6.D<sup>2</sup>PAK dimensions

Figure 13. D<sup>2</sup>PAK footprint (dimensions in mm)





			Dimensions				
		Ref.	Millin	Millimeters		hes	
i			Min.	Max.	Min.	Max.	
, <u>È</u> ,		Α	4.40	4.60	0.173	0.181	
		A1	2.40	2.72	0.094	0.107	
		b	0.61	0.88	0.024	0.035	
	D	b1	1.14	1.70	0.044	0.067	
		с	0.49	0.70	0.019	0.028	
	A1	c2	1.23	1.32	0.048	0.052	
	i i	D	8.95	9.35	0.352	0.368	
		е	2.40	2.70	0.094	0.106	
		e1	4.95	5.15	0.195	0.203	
· · · · · · · · · · · · · · · · · · ·	→ C	E	10	10.40	0.394	0.409	
li e1		L	13	14	0.512	0.551	
		L1	3.50	3.93	0.138	0.155	
		L2	1.27	1.40	0.050	0.055	

Table 7.I<sup>2</sup>PAK dimensions

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# 3 Ordering information

### Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS30SM60CT	STPS30SM60CT	TO-220AB	2.20 g	50	Tube
STPS30SM60CR	STPS30SM60CR	I <sup>2</sup> PAK	1.49 g	50	Tube
STPS30SM60CG-TR	STPS30SM60CG	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel

## 4 Revision history

Date	Revision	Changes
02-Nov-2011	1	First issue.



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